

**isc Silicon PNP Darlington Power Transistor**

**BDV64/A/B/C**

**DESCRIPTION**

- Collector Current  $-I_C = -12A$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = -2.0V(\text{Max.}) @ I_C = -5A$
- Complement to Type BDV65/A/B/C

**APPLICATIONS**

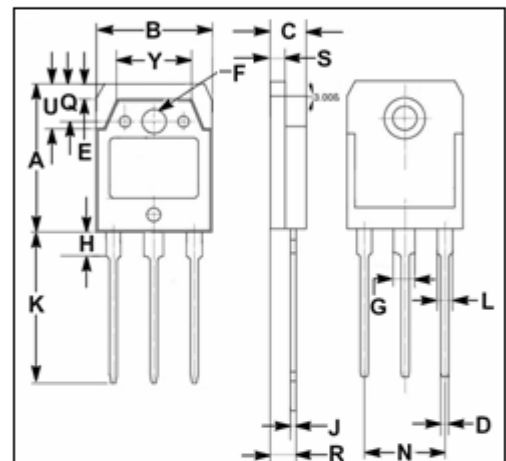
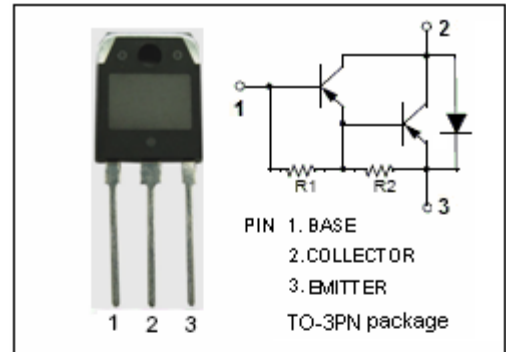
- Designed for audio output stages and general amplifier and switching applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	BDV64	-60	V
		BDV64A	-80	
		BDV64B	-100	
		BDV64C	-120	
$V_{CEO}$	Collector-Emitter Voltage	BDV64	-60	V
		BDV64A	-80	
		BDV64B	-100	
		BDV64C	-120	
$V_{EBO}$	Emitter-Base Voltage	-5	V	
$I_C$	Collector Current-Continuous	-12	A	
$I_{CM}$	Collector Current-Peak	-15	A	
$I_B$	Base Current-Continuous	-0.5	A	
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	125	W	
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3.5		
$T_J$	Junction Temperature	150	$^\circ\text{C}$	
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	35.7	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

## isc Silicon PNP Darlington Power Transistor

## BDV64/A/B/C

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	BDV64	$I_C = -30\text{mA}; I_B = 0$	-60			V	
		BDV64A		-80				
		BDV64B		-100				
		BDV64C		-120				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -20\text{mA}$			-2.0	V		
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -5\text{A}; V_{CE} = -4\text{V}$			-2.5	V		
$I_{CEO}$	Collector Cutoff Current	$V_{CE} = \frac{1}{2}V_{CE0max}; I_B = 0$			-2.0	mA		
$I_{CBO}$	Collector Cutoff Current	BDV64				-2.0	mA	
		BDV64A						$V_{CB} = -40\text{V}; I_E = 0; T_J = 150^\circ\text{C}$
		BDV64B						$V_{CB} = -50\text{V}; I_E = 0; T_J = 150^\circ\text{C}$
		BDV64C						$V_{CB} = -60\text{V}; I_E = 0; T_J = 150^\circ\text{C}$
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = V_{CBOmax}; I_E = 0$			-0.4	mA		
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-5	mA		
$h_{FE}$	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	1000					